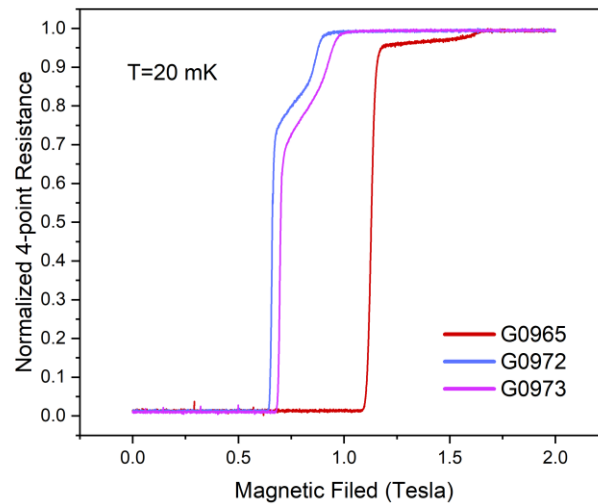


AFM scans of two aluminum layers grown on $\text{In}_{0.75}\text{Ga}_{0.25}\text{As}/\text{In}_{0.53}\text{Ga}_{0.47}\text{As}$ (6nm/100nm) on the $\text{InP}(001)$ substrate. **In both cases, the nominal thickness of the Al layer was 10 nm.**

- a. The layer was deposited at 0.5 \AA/s .
- b. The layer was deposited at 3.0 \AA/s .



Superconducting to normal phase transition signatures for three Al layers:

- G0972 was deposited at 3.0 \AA/s (10 nm thick)
- G0973 was deposited at 2.0 \AA/s (10 nm thick)
- G0965 was deposited at 2.0 \AA/s (8.6 nm thick)

Layers deposited at lower growth rates did not show superconductive behavior.